

PMST3906

40 V, 200 mA PNP switching transistor Rev. 05 — 29 April 2009

Product data sheet

Product profile

1.1 General description

PNP switching transistor in a SOT323 (SC-70) very small Surface-Mounted Device (SMD) plastic package.

NPN complement: PMST3904.

1.2 Features

Collector current: I_C ≤ -200 mA

Collector-emitter voltage: V_{CEO} ≤ -40 V

Very small SMD plastic package

1.3 Applications

General amplification and switching

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{CEO}	collector-emitter voltage	open base	-	-	-40	V
I _C	collector current		-	-	-200	mA

Pinning information

Table 2. **Pinning**

Pin	Description	Simplified outline	Graphic symbol
1	base		
2	emitter	3	3
3	collector		1—
		1 - 2	2
			sym013



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3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
PMST3906	SC-70	plastic surface-mounted package; 3 leads	SOT323	

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
PMST3906	*2A

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter	-	-40	V
V_{CEO}	collector-emitter voltage	open base	-	-40	V
V_{EBO}	emitter-base voltage	open collector	-	-6	V
I _C	collector current		-	-200	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-200	mA
I _{BM}	peak base current	single pulse; $t_p \le 1 \text{ ms}$	-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$	[1] -	200	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T_{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	-	625	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

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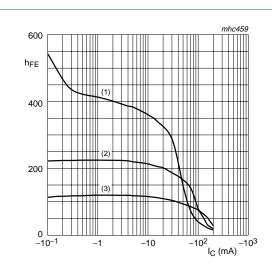
7. Characteristics

Table 7. Characteristics

 T_{amb} = 25 °C unless otherwise specified.

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I_{CBO}	collector-base cut-off current	$I_E = 0 \text{ A}; V_{CB} = -30 \text{ V}$	-	-	-50	nA
I _{EBO}	emitter-base cut-off current	$I_C = 0 A; V_{EB} = -6 V$	-	-	-50	nA
h _{FE}	DC current gain	$V_{CE} = -1 V$				
		$I_C = -0.1 \text{ mA}$	60	-	-	
		$I_C = -1 \text{ mA}$	80	-	-	
		$I_C = -10 \text{ mA}$	100	-	300	
		$I_C = -50 \text{ mA}$	60	-	-	
		$I_C = -100 \text{ mA}$	30	-	-	
V _{CEsat}	collector-emitter	$I_C = -10 \text{ mA}; I_B = -1 \text{ mA}$	-	-	-250	mV
	saturation voltage	$I_C = -50 \text{ mA}; I_B = -5 \text{ mA}$	-	-	-400	mV
V_{BEsat}	base-emitter saturation voltage	$I_C = -10 \text{ mA}; I_B = -1 \text{ mA}$	-	-	-850	mV
		$I_C = -50 \text{ mA}; I_B = -5 \text{ mA}$	-	-	-950	mV
t _d	delay time	$I_C = -10 \text{ mA};$	-	-	35	ns
t _r	rise time	$I_{Bon} = -1 \text{ mA};$	-	-	35	ns
t _{on}	turn-on time	I _{Boff} = 1 mA	-	-	70	ns
ts	storage time		-	-	225	ns
t _f	fall time		-	-	75	ns
t _{off}	turn-off time		-	-	300	ns
C _c	collector capacitance	$I_E = i_e = 0 \text{ A}; V_{CB} = -5 \text{ V};$ f = 1 MHz	-	-	4.5	pF
C _e	emitter capacitance	$I_C = I_c = 0 \text{ A};$ $V_{EB} = -500 \text{ mV};$ f = 1 MHz	-	-	10	pF
f _T	transition frequency	$I_C = -10 \text{ mA};$ $V_{CE} = -20 \text{ V};$ f = 100 MHz	250	-	-	MHz
NF	noise figure	$I_{C} = -100 \ \mu A;$ $V_{CE} = -5 \ V; \ R_{S} = 1 \ k\Omega;$ $f = 10 \ Hz \ to \ 15.7 \ kHz$	-	-	4	dB
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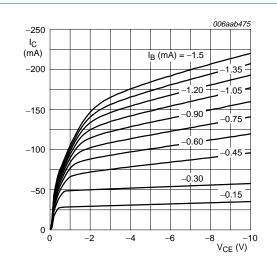
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$$V_{CE} = -1 V$$

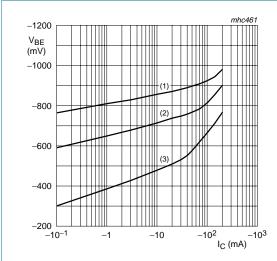
- (1) $T_{amb} = 150 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = -55 \, ^{\circ}C$

Fig 1. DC current gain as a function of collector current; typical values



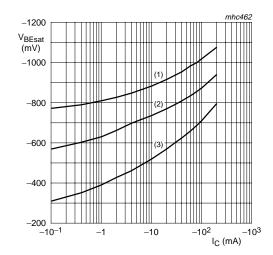
$$T_{amb} = 25 \, ^{\circ}C$$

Fig 2. Collector current as a function of collector-emitter voltage; typical values



- $V_{CE} = -1 \text{ V}$
- (1) $T_{amb} = -55 \, ^{\circ}C$
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 150 \, ^{\circ}C$

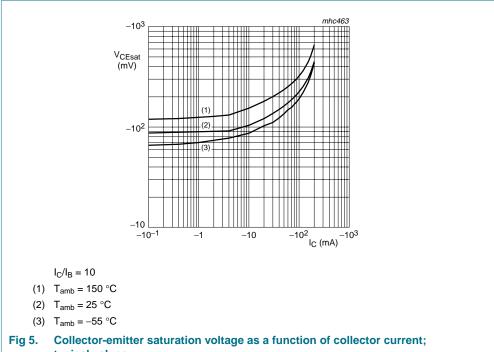
Fig 3. Base-emitter voltage as a function of collector current; typical values



- $I_{\rm C}/I_{\rm B} = 10$
- (1) $T_{amb} = -55$ °C
- (2) $T_{amb} = 25 \, ^{\circ}C$
- (3) $T_{amb} = 150 \, ^{\circ}C$

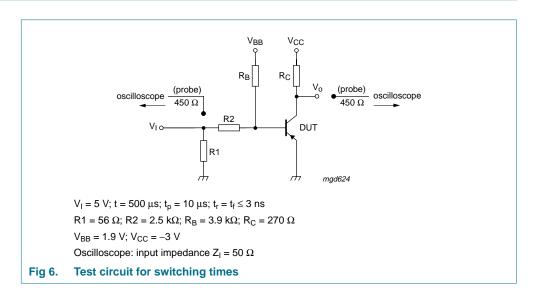
Fig 4. Base-emitter saturation voltage as a function of collector current; typical values

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typical values

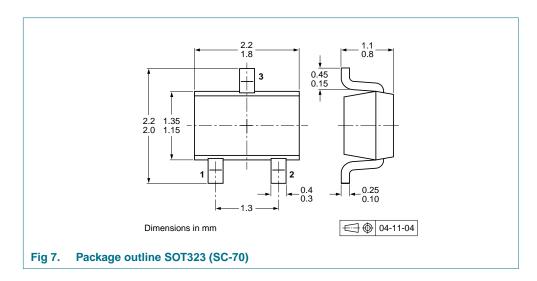
Test information



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Package outline



10. Packing information

Table 8. **Packing methods**

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity	
			3000	10000
PMST3906	SOT323	4 mm pitch, 8 mm tape and reel	-115	-135

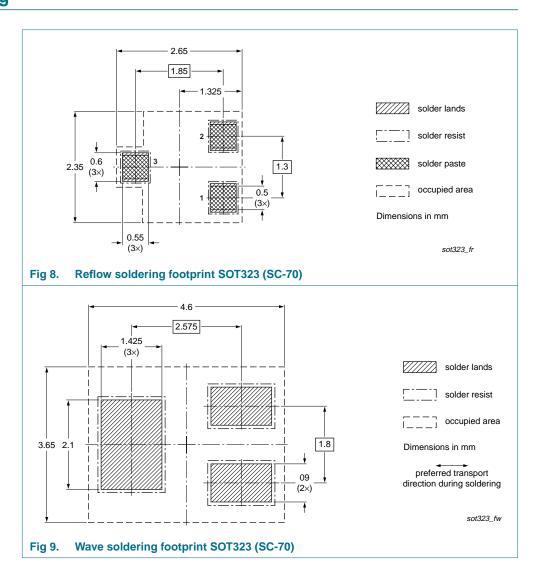
^[1] For further information and the availability of packing methods, see Section 14.

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11. Soldering



Product data sheet

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12. Revision history

Table 9. Revision history

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Document ID	Release date	Data sheet status	Change notice	Supersedes		
PMST3906_5	20090429	Product data sheet	-	PMST3906_4		
Modifications:		of this data sheet has been of NXP Semiconductors.	redesigned to comply v	vith the new identity		
	 Legal texts 	have been adapted to the n	new company name whe	ere appropriate.		
	 Figure 2: up 	odated				
	• Figure 5: fig	gure notes order amended				
	Section 10 "Packing information" added					
	Section 11 "Soldering": added					
	Section 13	"Legal information": updated	d			
PMST3906_4	20040121	Product specification	-	PMST3906_3		
PMST3906_3	19990422	Product specification	-	PMST3906_CNV_2		
PMST3906_CNV_2	19970527	Product specification	-	-		

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13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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